



40V MATCHED PAIR NPN SMALL SIGNAL TRANSISTOR IN SOT363

Features

- BVceo > 40V
- I_C = 200mA High Collector Current
- Pair of NPN Transistors that are Intrinsically Matched (Note 1)
- 2% Matching on Current Gain (h_{FE})
- 2mV Matching on Base-Emitter Voltage (V_{BE})
- Fully Internally Isolated in a Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 2 & 3)
- Halogen and Antimony Free. "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 5)

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.006 grams (Approximate)

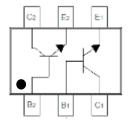
Applications

- Current Mirrors
- Differential and Instrumentation Amplifiers
- Comparators



SOT363

Top View



Device Schematic and Pin-Out Top View

Ordering Information (Notes 5 & 6)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMMT3904W-7-F	AEC-Q101	K4A	7	8	3,000
DMMT3904WQ-7-F	Automotive	K4A	7	8	3,000

Notes:

1. Intrinsically matched pair as this is built with adjacent die from the same wafer.

2. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

3. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

4. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

5. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

6. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

7	0010	0040	0000	0004	0000	0000	0004	000
		•	К4А	M M	YM = Y = Y	Date Cod ear (ex: F	Type Markin e Marking = 2018) 2 = Februar	0
			SOT363					

Date Code Key

Date Code Rey												
Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	E	F	G	Н	I	J	K	L	М	N	0	Р
Manth	lan	F ab	Max	A	Mari	l			a Com	Oct	Neur	Dee
Month	Jan	Feb	Mar	Apr	May	Jun	JL	II Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	Ιc	200	mA

Thermal Characteristics – Total Device (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7) Total Device	PD	200	mW
Thermal Resistance, Junction to Ambient (Note 7)	R _{0JA}	625	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-65 to +150	°C

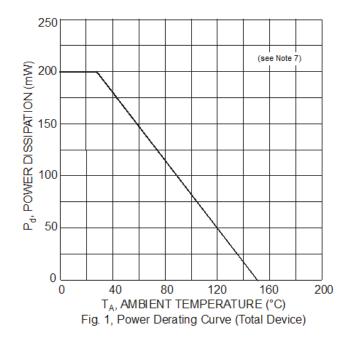
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 7. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics – Total Device





Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS				1		
Collector-Base Breakdown Voltage	BV _{CBO}	60			V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage(Note 9)	BV _{CEO}	40	_	_	V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0			V	$I_{E} = 100 \mu A, I_{C} = 0$
Collector Cutoff Current	ICEX	_	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
Base Cutoff Current	I _{BL}	_		50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$
ON CHARACTERISTICS (Note 9)			•		•	
DC Current Gain	hfe	40 70 100 60 30		 300 		$ \begin{array}{ll} I_{C} = & 100 \mu A, \ V_{CE} = & 1.0 V \\ I_{C} = & 1.0 m A, \ V_{CE} = & 1.0 V \\ I_{C} = & 10 m A, \ V_{CE} = & 1.0 V \\ I_{C} = & 50 m A, \ V_{CE} = & 1.0 V \\ I_{C} = & 100 m A, \ V_{CE} = & 1.0 V \\ \end{array} $
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—		200 300	mV	$I_{C} = 10mA, I_{B} = 1.0mA$ $I_{C} = 50mA, I_{B} = 5.0mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	_	850 950	mV	$I_{C} = 10$ mA, $I_{B} = 1.0$ mA $I_{C} = 50$ mA, $I_{B} = 5.0$ mA
MATCHING CHARACTERISTICS						
DC Current Gain Matching (Note 10)	h _{FE1} / h _{FE2}	_	1	2	%	$I_C = 2mA$, $V_{CE} = 5V$
Base-Emitter Voltage Matching (Note 11)	V _{BE1} - V _{BE2}	_	1	2	mV	$I_C = 2mA$, $V_{CE} = 5V$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)1} / V _{CE(SAT)2}	_	1	2	%	I _C = 10mA, I _B = 1.0mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)1} / V _{BE(SAT)2}	_	1	2	%	I _C = 10mA, I _B = 1.0mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{OBO}	_	_	4.0	pF	$V_{CB} = 5.0V, f = 1.0MHz, I_E = 0$
Input Capacitance	C _{IBO}	_	_	8.0	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$
Input Impedance	hıE	1.0	_	10	kΩ	
Voltage Feedback Ratio	h _{RE}	0.5		8	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h _{FE}	100	_	400		f = 1.0 kHz
Output Admittance	h _{OE}	1.0		40	μS	
Current Gain-Bandwidth Product	f⊤	300	—	_	MHz	$V_{CE} = 20V$, $I_C = 10mA$, f = 100MHz
Noise Figure	NF	—	—	5.0	dB	$\label{eq:VCE} \begin{split} V_{CE} &= 5.0V, \ I_C = 100 \mu A, \\ R_S &= 1.0 k \Omega, \ f = 1.0 k Hz \end{split}$
SWITCHING CHARACTERISTICS						
Delay Time	t _D	_	—	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	t _R		—	35	ns	$V_{BE(OFF)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	ts			200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	t _F	_	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Notes:

9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%. 10. Is the ratio of one transistor compared to the other transistor.

11. V_{BE1} - V_{BE2} is the absolute difference of one transistor compared to the other transistor.



100

f = 1MHz

Cobo

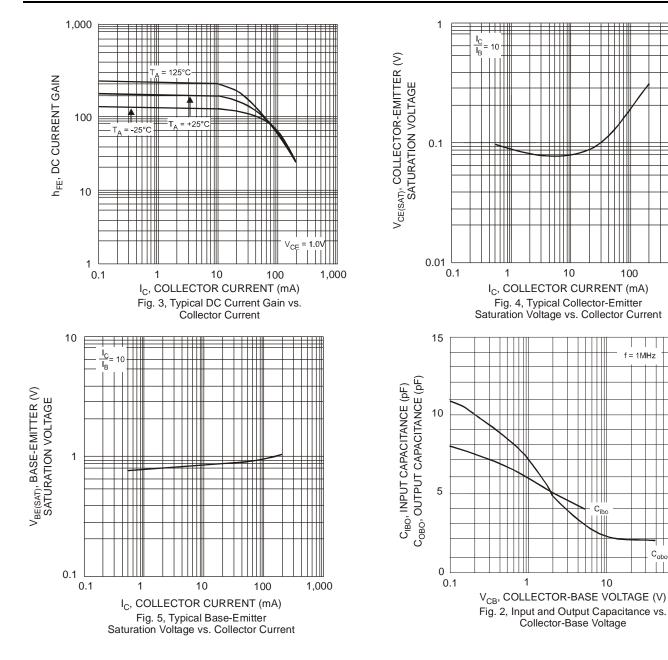
100

Cibo

10

1,000

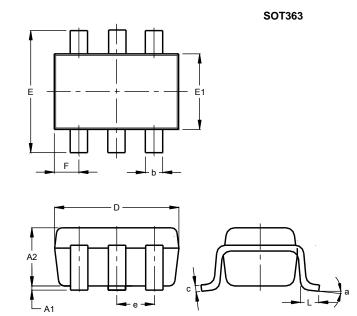
Typical Electrical Characteristics (@T_A = +25°C unless otherwise specified.)





Package Outline Dimensions

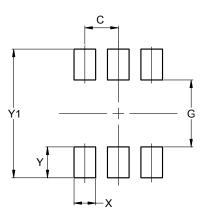
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	1.00				
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C).650 B	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	Dimen	sions	in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500

SOT363



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